

# RGTH50TS65

## 650V 25A Field Stop Trench IGBT

| V <sub>CES</sub>            | 650V |
|-----------------------------|------|
| I <sub>C(100°C)</sub>       | 25A  |
| V <sub>CE(sat) (Typ.)</sub> | 1.6V |
| $P_{D}$                     | 174W |

#### Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

### Applications

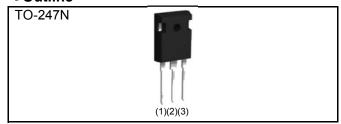
**PFC** 

**UPS** 

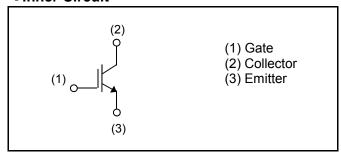
**Power Conditioner** 

ΙH

#### Outline



#### ●Inner Circuit



Packaging Specifications

|      | Packaging                 | Tube       |
|------|---------------------------|------------|
|      | Reel Size (mm)            | -          |
| Typo | Tape Width (mm)           | -          |
| Туре | Basic Ordering Unit (pcs) | 450        |
|      | Packing code              | C11        |
|      | Marking                   | RGTH50TS65 |

#### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

| Parameter                      |                        | Symbol             | Value       | Unit |
|--------------------------------|------------------------|--------------------|-------------|------|
| Collector - Emitter Voltage    |                        | V <sub>CES</sub>   | 650         | V    |
| Gate - Emitter Voltage         |                        | $V_{GES}$          | ±30         | V    |
| Callactor Current              | T <sub>C</sub> = 25°C  | I <sub>C</sub>     | 50          | А    |
| Collector Current              | T <sub>C</sub> = 100°C | I <sub>C</sub>     | 25          | А    |
| Pulsed Collector Current       |                        | I <sub>CP</sub> *1 | 100         | А    |
| Dower Dissination              | T <sub>C</sub> = 25°C  | P <sub>D</sub>     | 174         | W    |
| Power Dissipation              | T <sub>C</sub> = 100°C | P <sub>D</sub>     | 87          | W    |
| Operating Junction Temperature |                        | T <sub>j</sub>     | -40 to +175 | °C   |
| Storage Temperature            |                        | T <sub>stg</sub>   | -55 to +175 | °C   |

<sup>\*1</sup> Pulse width limited by T<sub>imax.</sub>

#### ●Thermal Resistance

| Parameter                               | Symbol            | Values |      |      | Unit  |
|---|-------------------|--------|------|------|-------|
| raiailletei                             |                   | Min.   | Тур. | Max. | Offic |
| Thermal Resistance IGBT Junction - Case | $R_{\theta(j-c)}$ | ı      | 1    | 0.86 | °C/W  |

## ullet IGBT Electrical Characteristics (at $T_j$ = 25°C unless otherwise specified)

| Parameter                                 | Symbol               | Conditions   | Values |            |          | Unit  |
|---|----------------------|--|--------|------------|----------|-------|
| r ai ainietei                             | Syllibol             |  | Min.   | Тур.       | Max.     | Offic |
| Collector - Emitter Breakdown<br>Voltage  | BV <sub>CES</sub>    | $I_{C} = 10 \mu A, V_{GE} = 0 V$                                   | 650    | 1          | 1        | V     |
| Collector Cut - off Current               | I <sub>CES</sub>     | V <sub>CE</sub> = 650V, V <sub>GE</sub> = 0V                       | 1      | ı          | 10       | μΑ    |
| Gate - Emitter Leakage Current            | I <sub>GES</sub>     | $V_{GE} = \pm 30V, V_{CE} = 0V$                                    | ı      | ı          | ±200     | nA    |
| Gate - Emitter Threshold<br>Voltage       | $V_{\text{GE(th)}}$  | V <sub>CE</sub> = 5V, I <sub>C</sub> = 17.5mA                      | 4.5    | 5.5        | 6.5      | V     |
| Collector - Emitter Saturation<br>Voltage | V <sub>CE(sat)</sub> | $I_C = 25A, V_{GE} = 15V$ $T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$ | -      | 1.6<br>2.1 | 2.1<br>- | V     |

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

| Parameter                        | Symbol              | Conditions                                    | Values |         |      | Unit  |
|----------------------------------|---------------------|---|--------|---------|------|-------|
| Farameter                        | Symbol              | Conditions                                    | Min.   | Тур.    | Max. | Offic |
| Input Capacitance                | C <sub>ies</sub>    | V <sub>CE</sub> = 30V                         | -      | 1410    | -    |       |
| Output Capacitance               | C <sub>oes</sub>    | V <sub>GE</sub> = 0V                          | -      | 57      | -    | pF    |
| Reverse Transfer Capacitance     | C <sub>res</sub>    | f = 1MHz                                      | -      | 22      | -    |       |
| Total Gate Charge                | Q <sub>g</sub>      | V <sub>CE</sub> = 300V                        | -      | 49      | -    |       |
| Gate - Emitter Charge            | $Q_ge$              | I <sub>C</sub> = 25A                          | -      | 15      | -    | nC    |
| Gate - Collector Charge          | $Q_{gc}$            | V <sub>GE</sub> = 15V                         | -      | 19      | -    |       |
| Turn - on Delay Time             | t <sub>d(on)</sub>  | I <sub>C</sub> = 25A, V <sub>CC</sub> = 400V  | -      | 27      | -    |       |
| Rise Time                        | t <sub>r</sub>      | $V_{GE} = 15V, R_G = 10\Omega$                | -      | 38      | -    |       |
| Turn - off Delay Time            | t <sub>d(off)</sub> | T <sub>j</sub> = 25°C                         | -      | 94      | -    | ns    |
| Fall Time                        | t <sub>f</sub>      | Inductive Load                                | -      | 50      | -    |       |
| Turn - on Delay Time             | t <sub>d(on)</sub>  | I <sub>C</sub> = 25A, V <sub>CC</sub> = 400V  | -      | 27      | -    |       |
| Rise Time                        | t <sub>r</sub>      | $V_{GE} = 15V, R_G = 10\Omega$                | -      | 38      | -    |       |
| Turn - off Delay Time            | t <sub>d(off)</sub> | T <sub>j</sub> = 175°C                        | -      | 107     | -    | ns    |
| Fall Time                        | t <sub>f</sub>      | Inductive Load                                | -      | 65      | -    |       |
|                                  |                     | I <sub>C</sub> = 100A, V <sub>CC</sub> = 520V |        |         |      |       |
| Reverse Bias Safe Operating Area | RBSOA               | $V_P = 650V, V_{GE} = 15V$                    | FU     | LL SQUA | RE   | -     |
|                                  |                     | $R_G = 60\Omega, T_j = 175^{\circ}C$          |        |         |      |       |

#### **•**Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

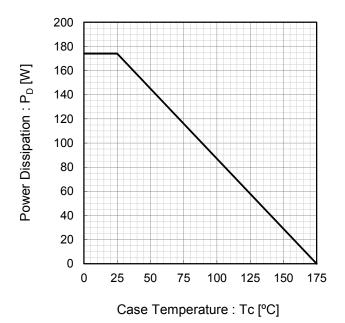


Fig.2 Collector Current vs. Case Temperature

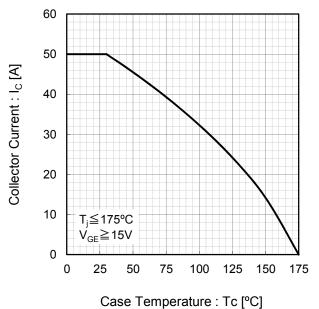


Fig.3 Forward Bias Safe Operating Area

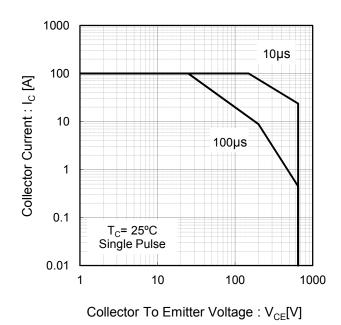
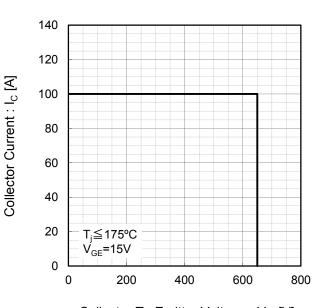


Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

#### • Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

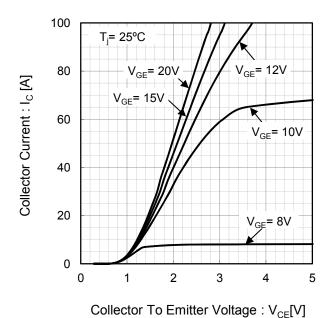
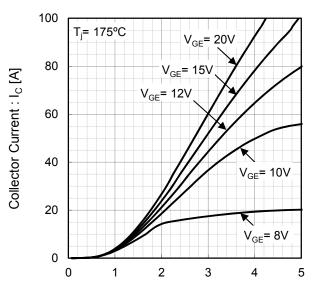


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.7 Typical Transfer Characteristics

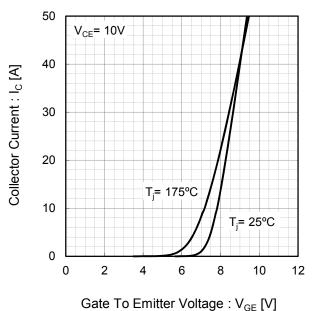
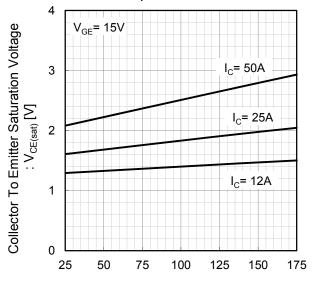


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

#### Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

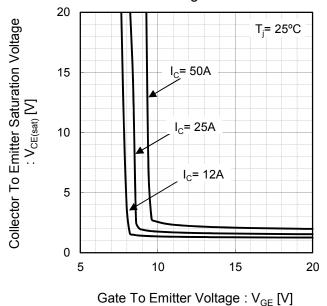
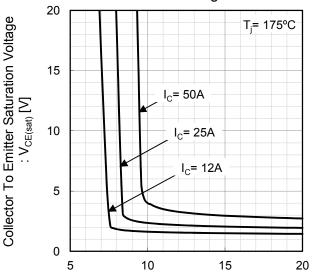


Fig. 10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage :  $V_{GE}[V]$ 

Fig.11 Typical Switching Time vs. Collector Current

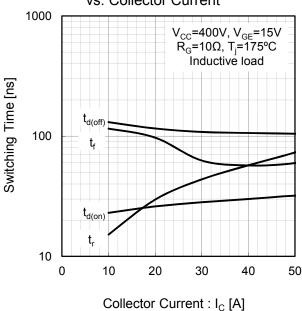
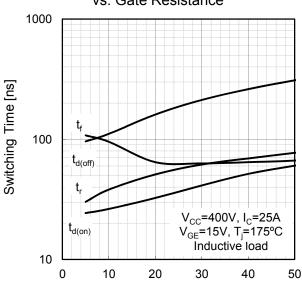


Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance :  $R_G[\Omega]$ 

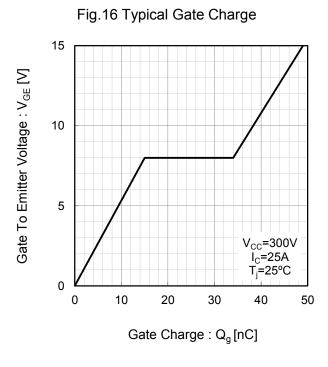
#### • Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$ E<sub>or</sub> 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V R<sub>G</sub>=10 $\Omega$ , T<sub>j</sub>=175°C Inductive load 0.01 0 10 20 30 40 50 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $\mathsf{E}_{\mathsf{off}}$ 1 0.1 V<sub>CC</sub>=400V, I<sub>C</sub>=25A V<sub>GE</sub>=15V, T<sub>j</sub>=175°C Inductive load 0.01 10 0 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

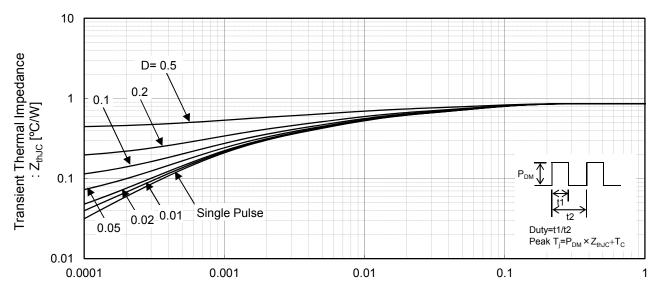
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 10 Cres f=1MHz V<sub>GE</sub>=0V 25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]



#### • Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]



Data Sheet RGTH50TS65

### ●Inductive Load Switching Circuit and Waveform

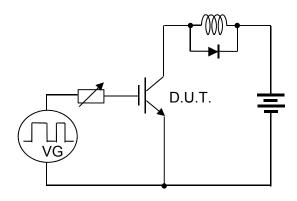


Fig.18 Inductive Load Circuit

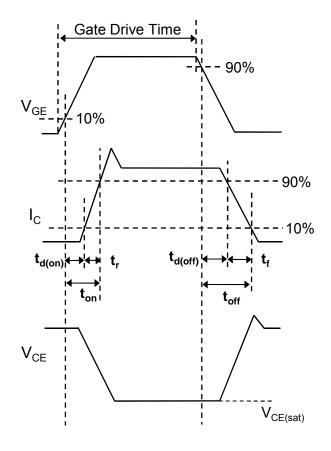


Fig.19 Inductive Load Waveform

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# RGTH50TS65 - Web Page

**Distribution Inventory** 

| Part Number                 | RGTH50TS65 |
|-----------------------------|------------|
| Package                     | TO-247N    |
| Unit Quantity               | 450        |
| Minimum Package Quantity    | 450        |
| Packing Type                | Bulk       |
| Constitution Materials List | inquiry    |
| RoHS                        | Yes        |

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